

Spice Project

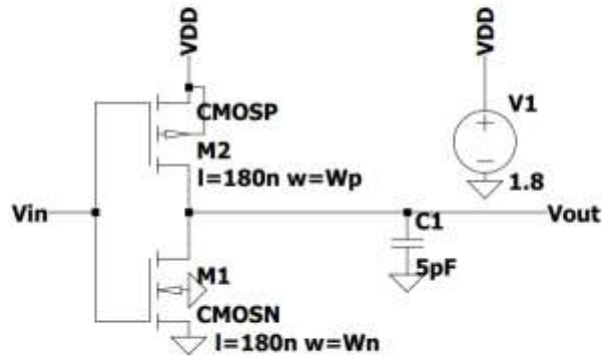
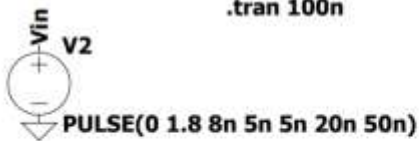
EE619A

Group Members

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KRISHNA SATPUTE

```
.meas TRAN t_hl TRIG V(Vout)=1.62 TD=0 FALL=1 TARG V(Vout)=0.18 TD=0 FALL=1
.meas TRAN t_lh TRIG V(Vout)=.18 TD=0 RISE=1 TARG V(Vout)=1.62 TD=0 RISE=1
```

```
.lib tsmc018.lib
;dc V2 0 1.8 0.01
.tran 100n
```



```
.param Wp=2.77*Wn
.step param Wn 240n 960n 240n
```

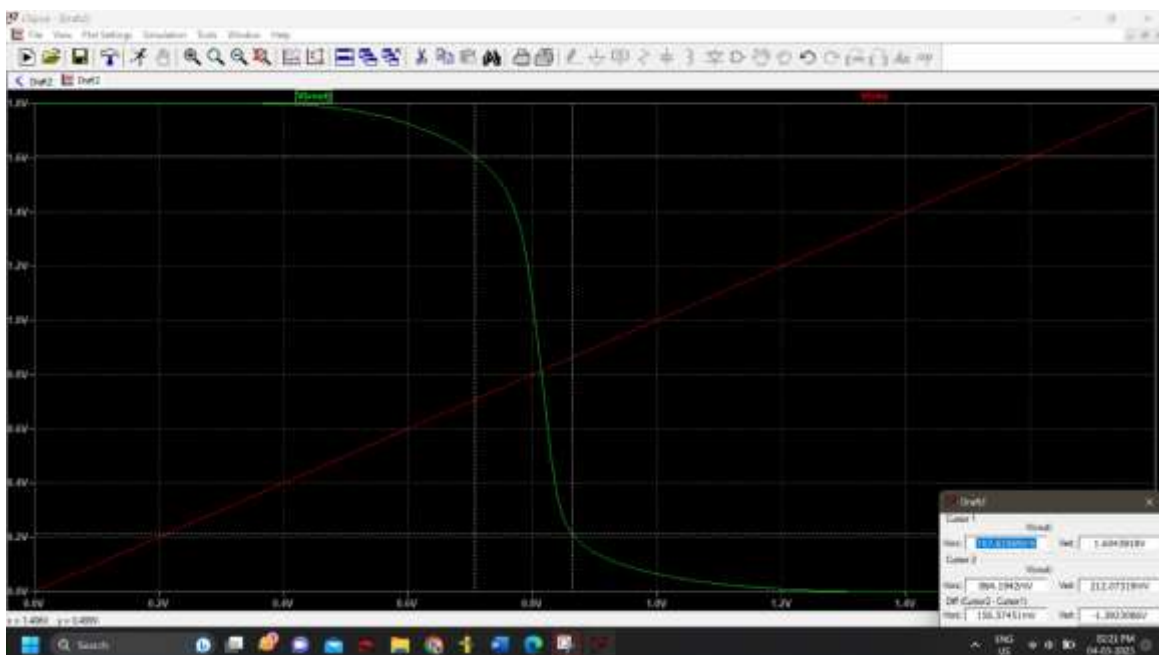
Circuit Parameters

NMOS $l = 180 \text{ nm}, W = W_n$

PMOS $l = 180 \text{ nm}, W = W_p$

$V_{DD} = 1.8 \text{ V}$

a) After analysis, we got PMOS to NMOS size ratio of the minimum-sized CMOS inverter to have equal rise and fall time as 2.77



Using the Slope = -1 criteria,

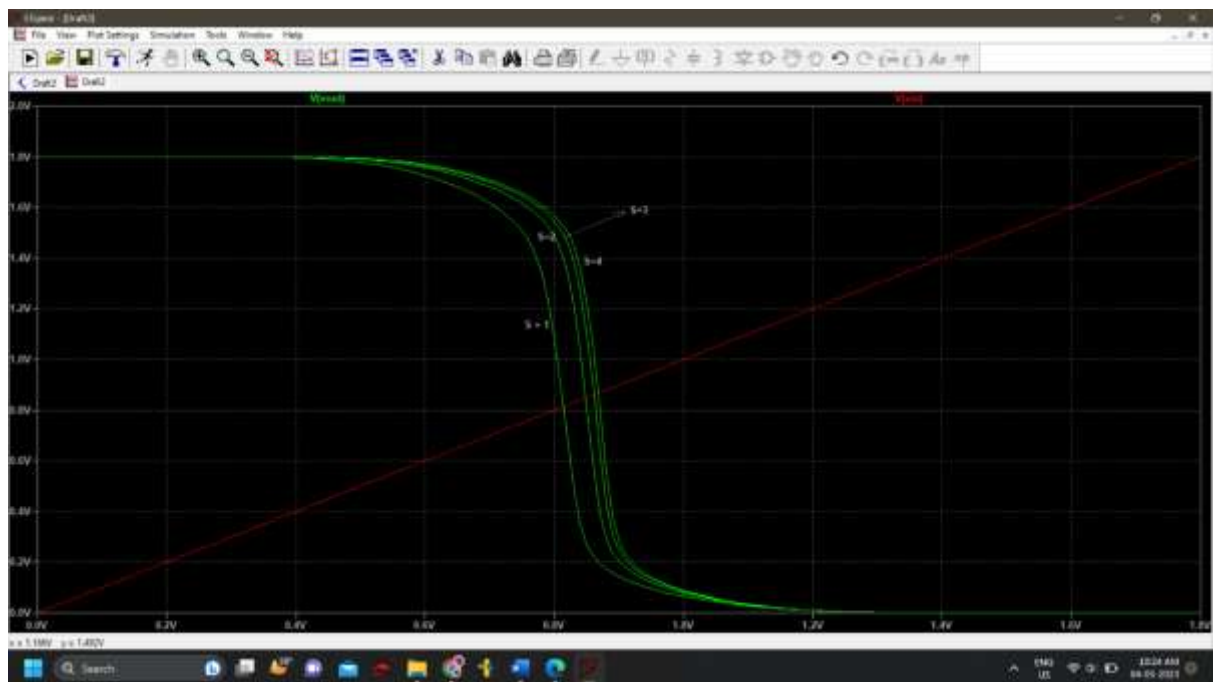
$$V_{IL} = 0.7, V_{OH} = 1.6$$

$$V_{IH} = 0.86, V_{OL} = 0.2$$

$$NM_H = V_{OH} - V_{IH} = 0.74$$

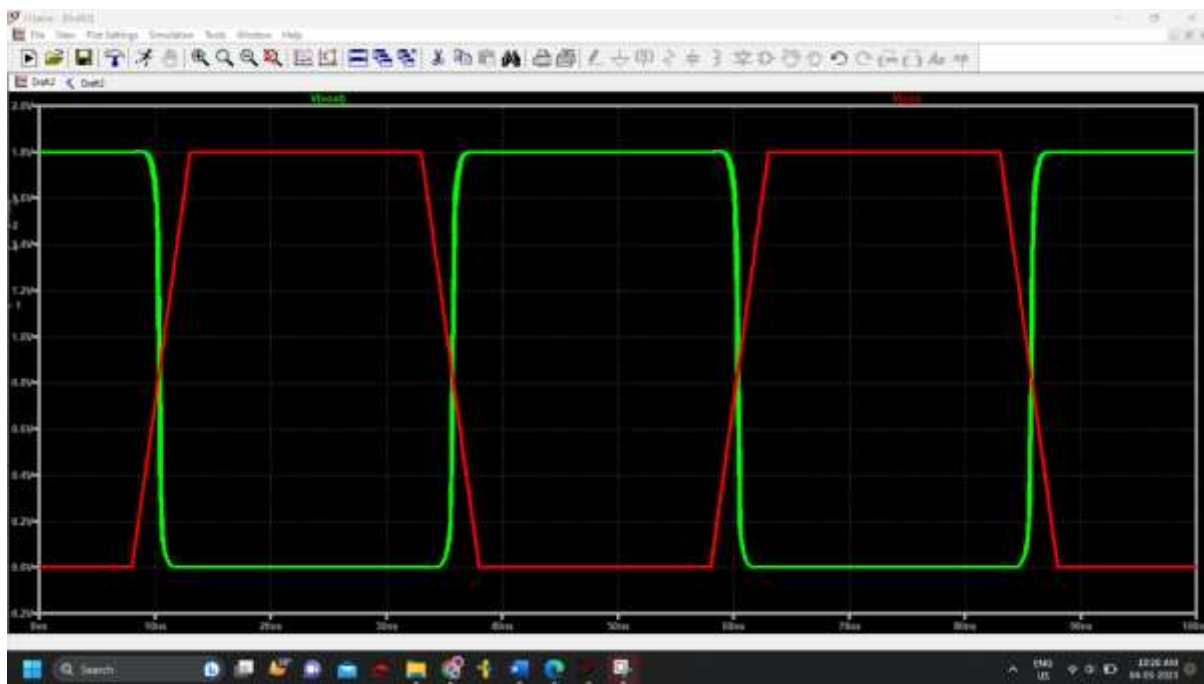
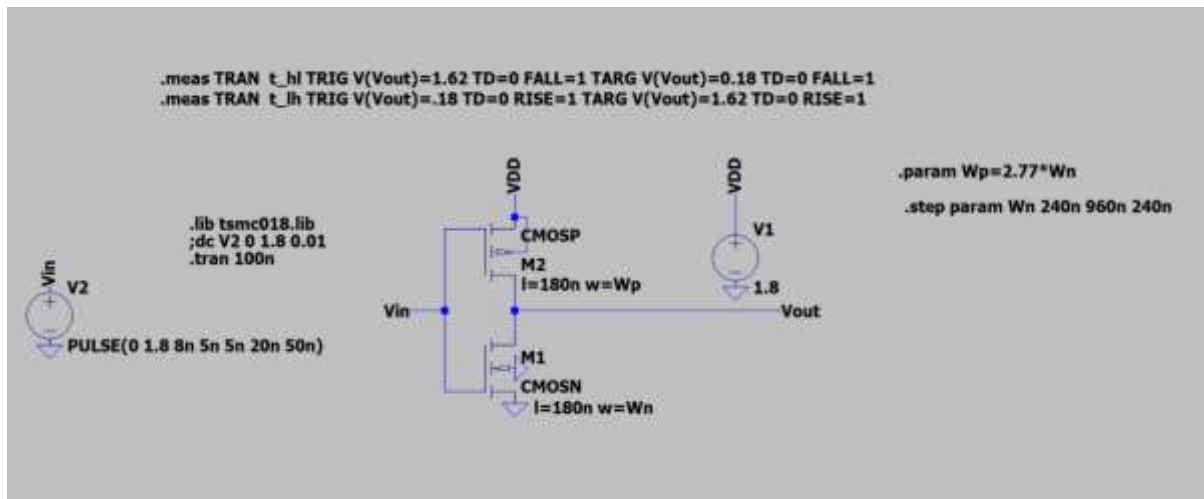
$$NM_L = V_{IL} - V_{OL} = 0.5$$

$$NM = \min(NM_L, NM_H) = 0.5$$



b. Transient analysis result (Vout vs Vin)

Case1. No external capacitor is attached



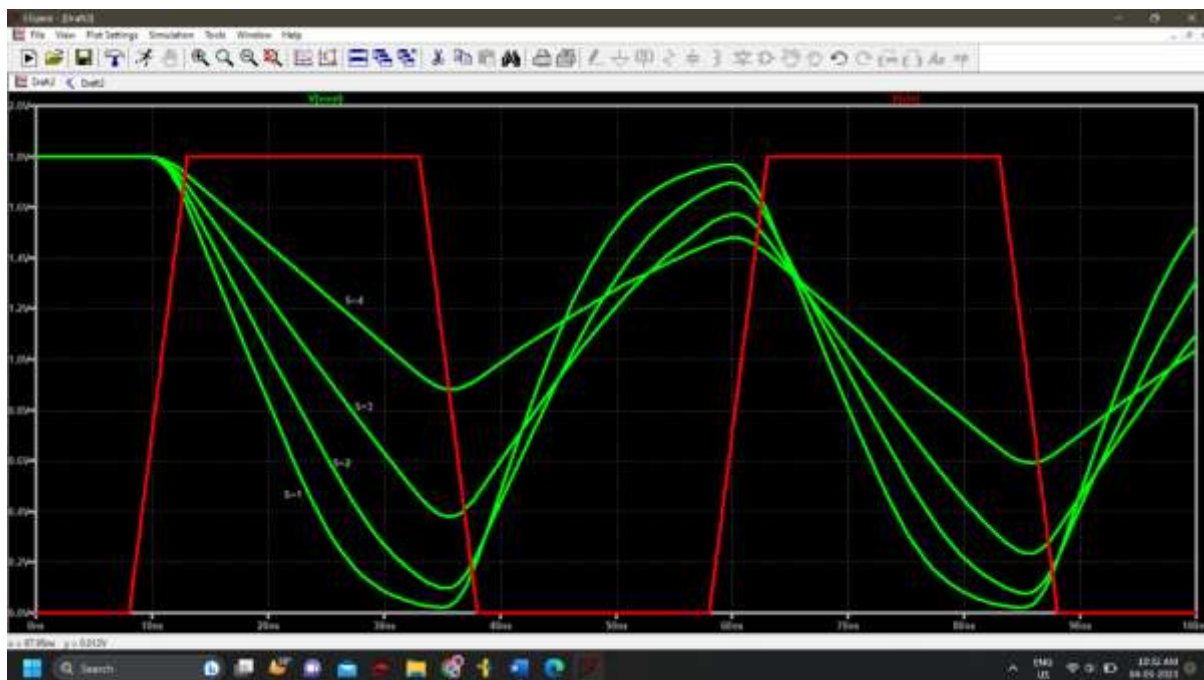
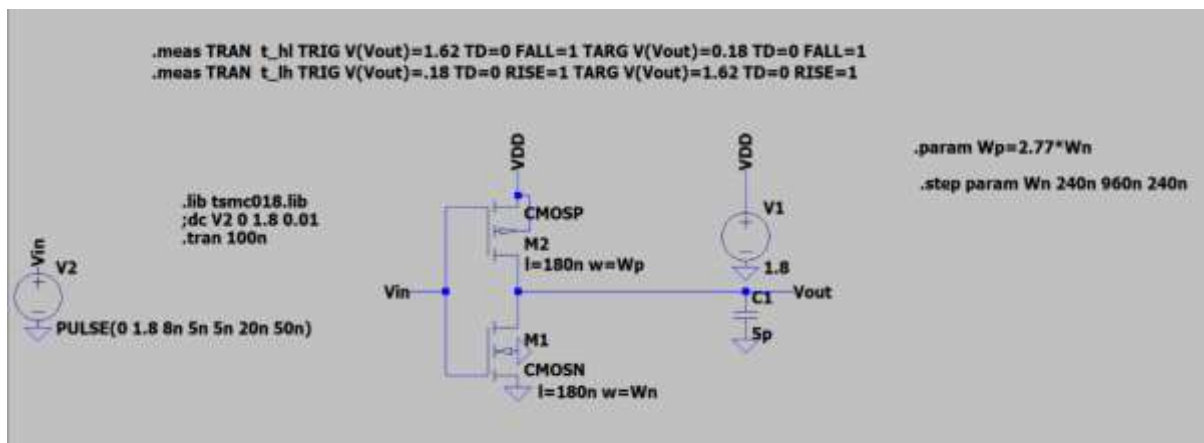
Measurement: t_hl

step	t_hl	FROM	TO
1	5.49759e-10	9.93779e-09	1.04875e-08
2	5.09718e-10	1.00763e-08	1.05861e-08
3	5.18332e-10	1.01232e-08	1.06416e-08
4	5.1002e-10	1.01477e-08	1.06578e-08

Measurement: t_lh

step	t_lh	FROM	TO
1	5.42293e-10	3.55436e-08	3.60859e-08
2	5.00775e-10	3.54539e-08	3.59547e-08
3	4.76966e-10	3.5431e-08	3.5908e-08
4	4.6912e-10	3.54116e-08	3.58807e-08

Case2. When an external capacitor of 5 pF is attached to the output node



Measurement: t_hl

step	t_hl	FROM	TO
1	0	1.57354e-08	0
2	0	1.4081e-08	0
3	1.86152e-08	1.33187e-08	3.1934e-08
4	1.45721e-08	1.28848e-08	2.74569e-08

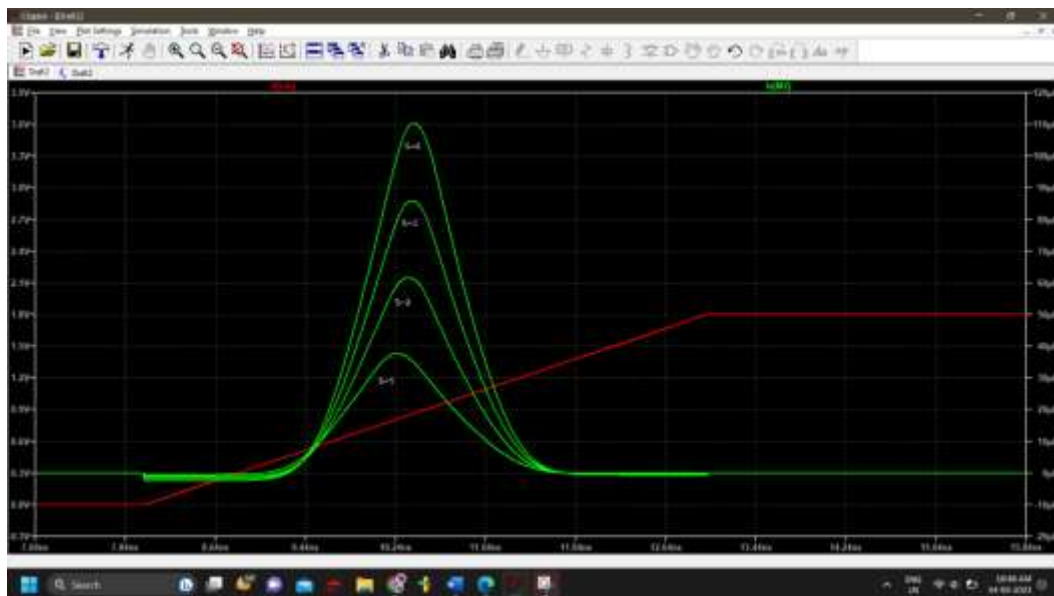
Measurement: t_lh

step	t_lh	FROM	TO
1	0	0	0
2	0	0	0
3	1.8836e-08	3.73715e-08	5.62075e-08
4	1.42217e-08	3.77328e-08	5.19545e-08

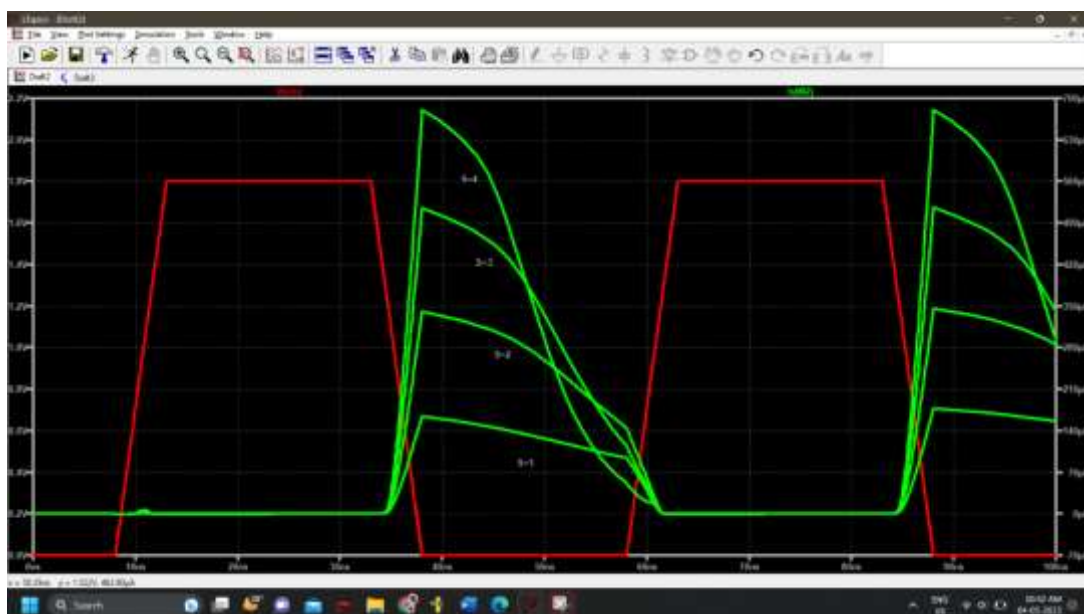
As we are increasing the value of W_n and W_p the resistance is getting decreased so, the time constant also reduces. So, the capacitor is getting charged at a faster rate.

Current drawn from the power supply in all cases as the input voltage is swept slowly w.r.t the output

Without capacitor

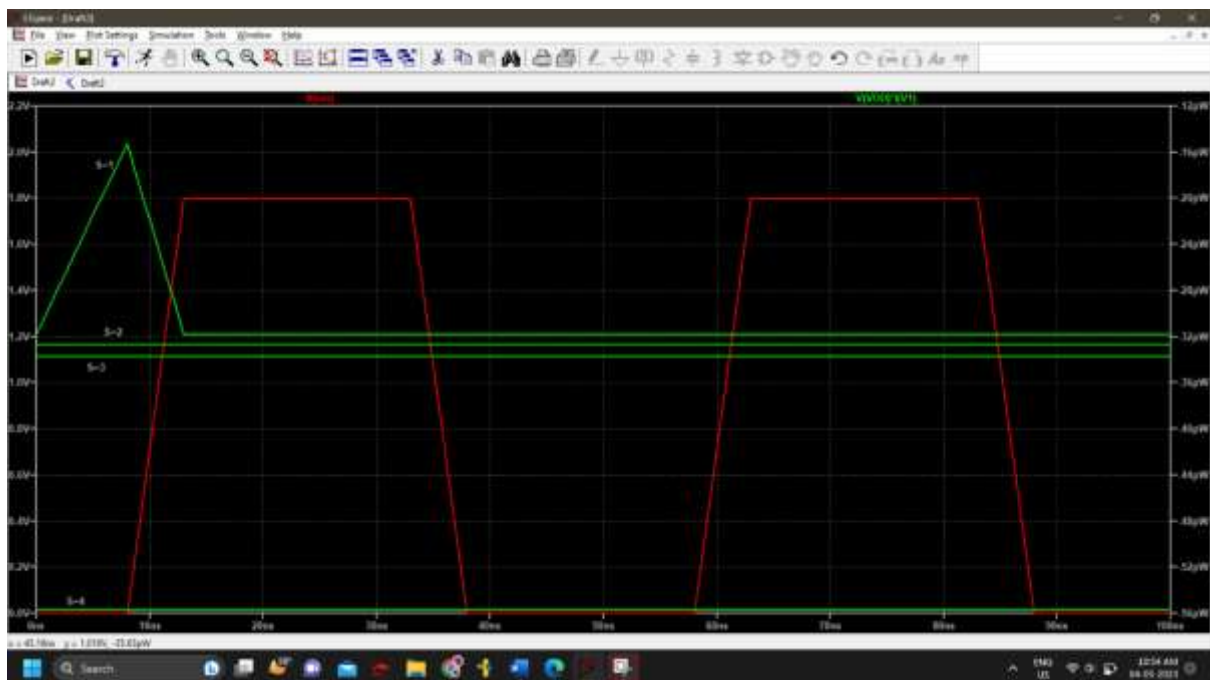


With capacitor

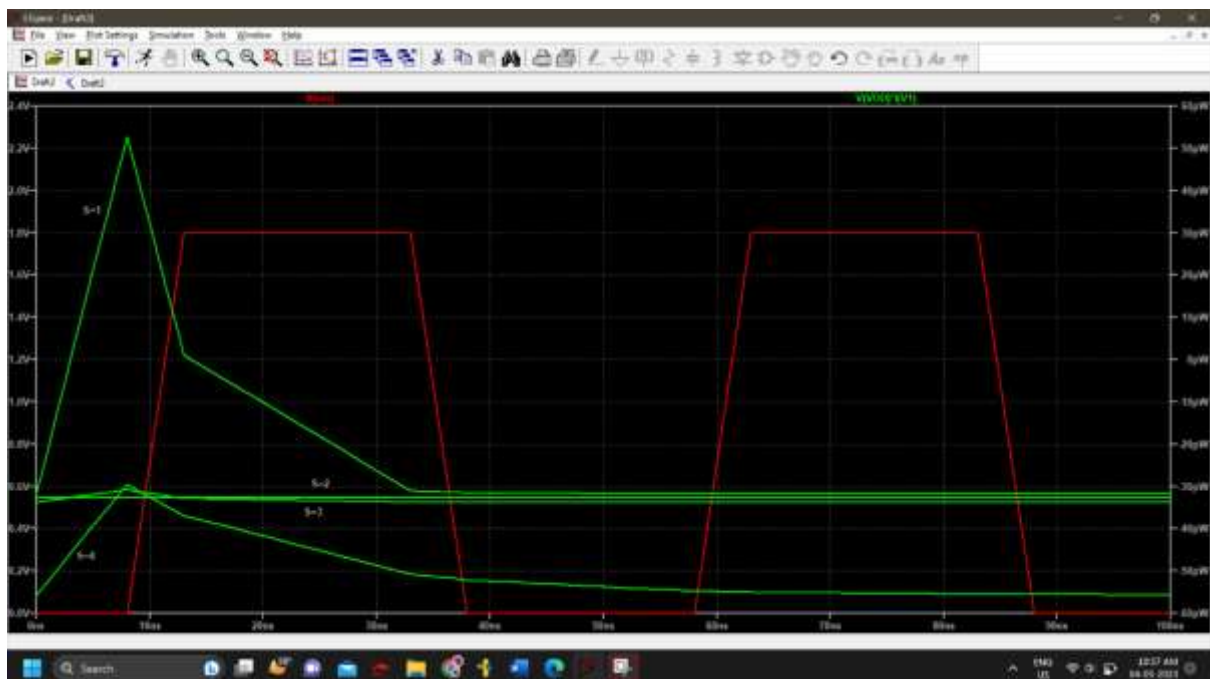


Static Power dissipation

Without capacitor

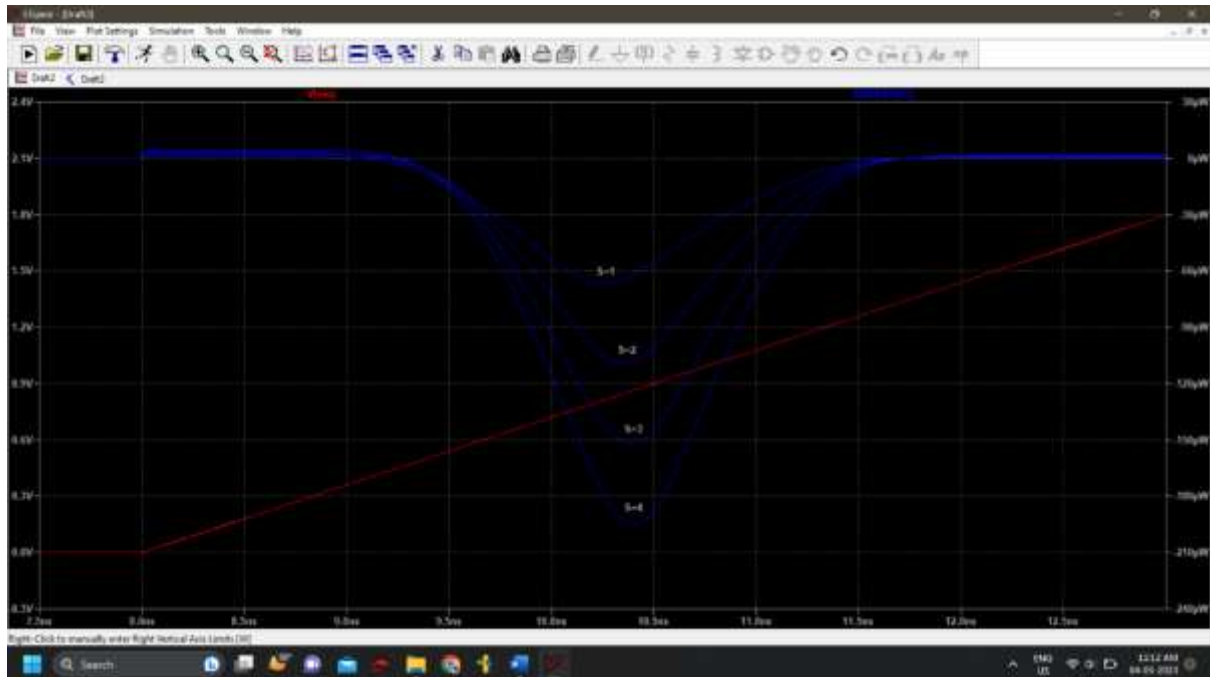


With capacitor

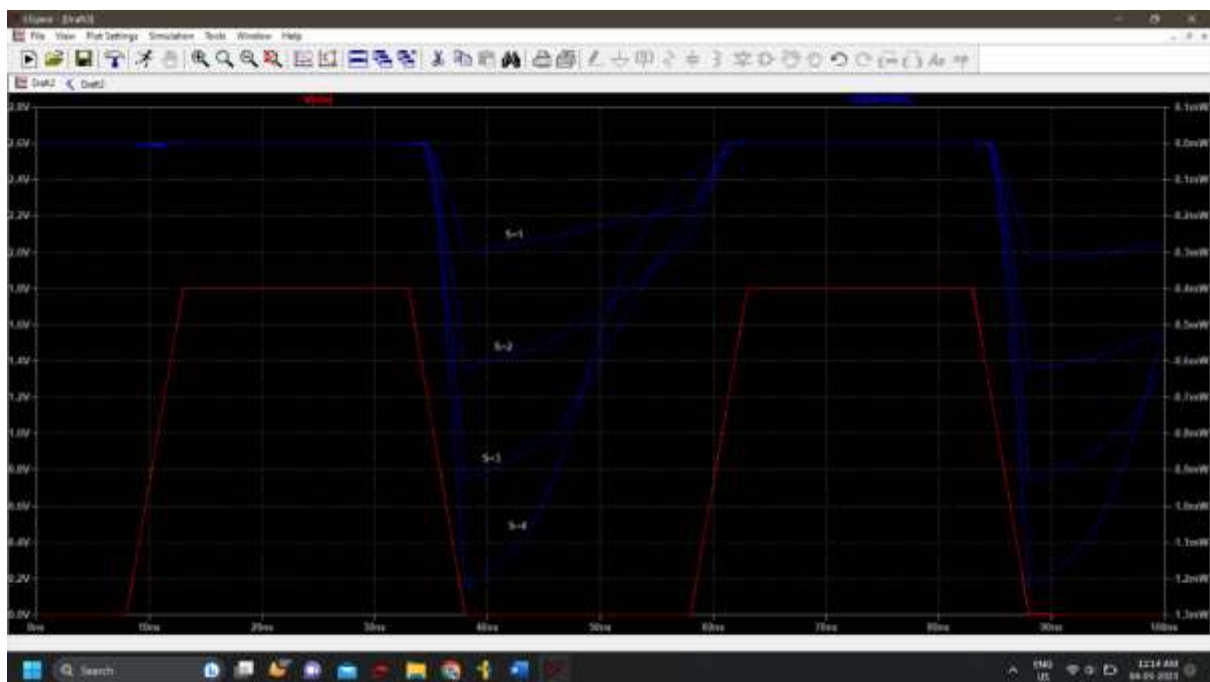


Dynamic power dissipation

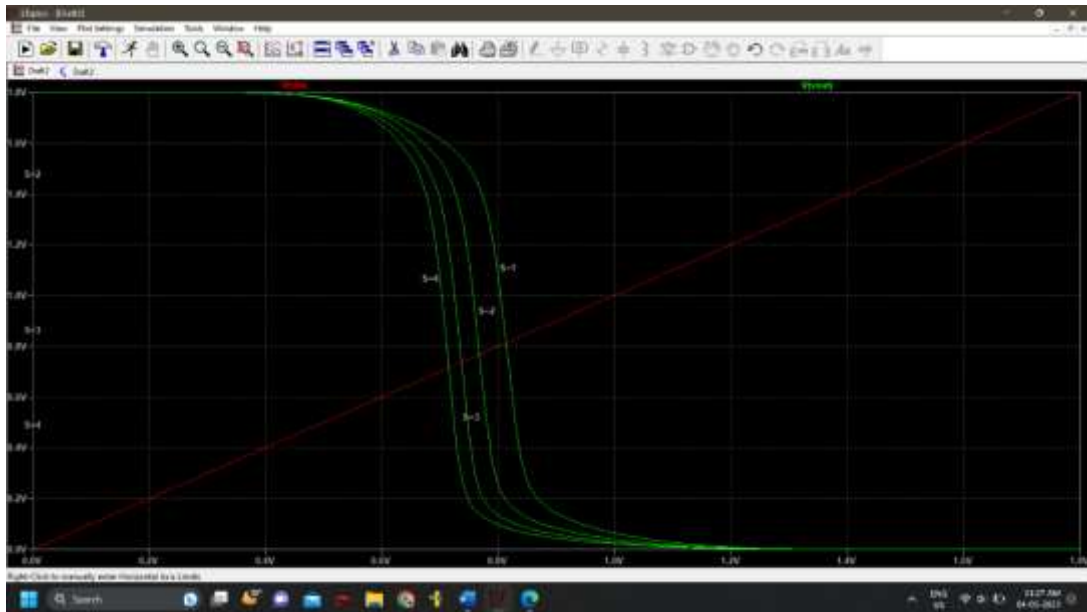
Without capacitor



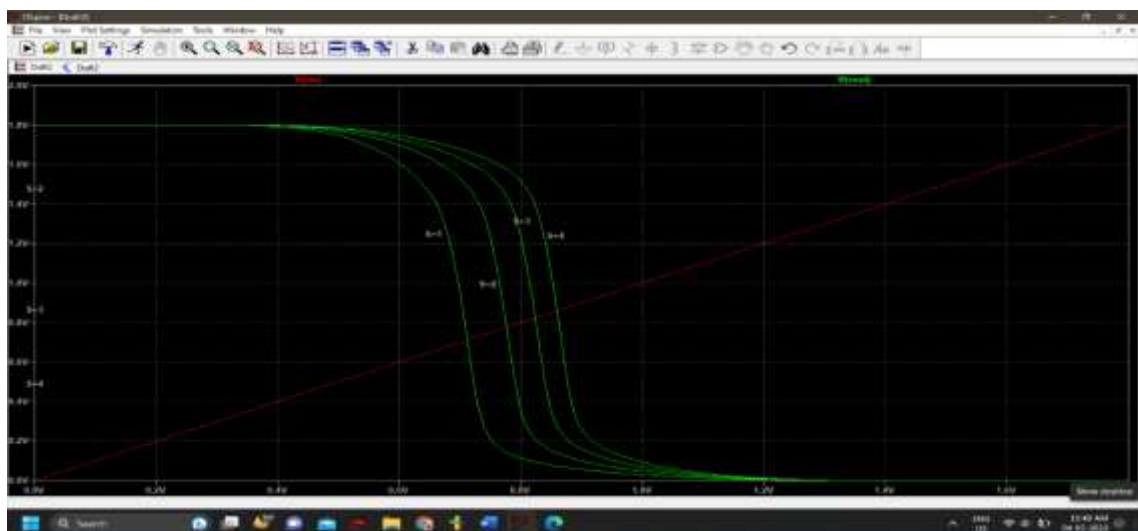
With capacitor



c) Simulate the static VTC of an inverter in which the NMOS is sized K_n times the size of the corresponding NMOS of the minimum-sized inverter for $K_n = 1, 2, 4$, keeping the size of the PMOS the same as that of the corresponding PMOS of the minimum-sized inverter.



ii. simulate the static VTC of an inverter in which the PMOS is sized K_p times the size of the corresponding PMOS of the minimum-sized inverter for $K_p = 1, 2, 4$, keeping the size of the NMOS the same as that of the corresponding NMOS of the minimum-sized inverter.



d) Transient analysis

When PMOS is sized K_p times the size of the corresponding PMOS of the minimum-sized inverter for $K_p = 1, 2, 4$, keeping the size of the NMOS the same as that of the corresponding NMOS of the minimum-sized inverter.

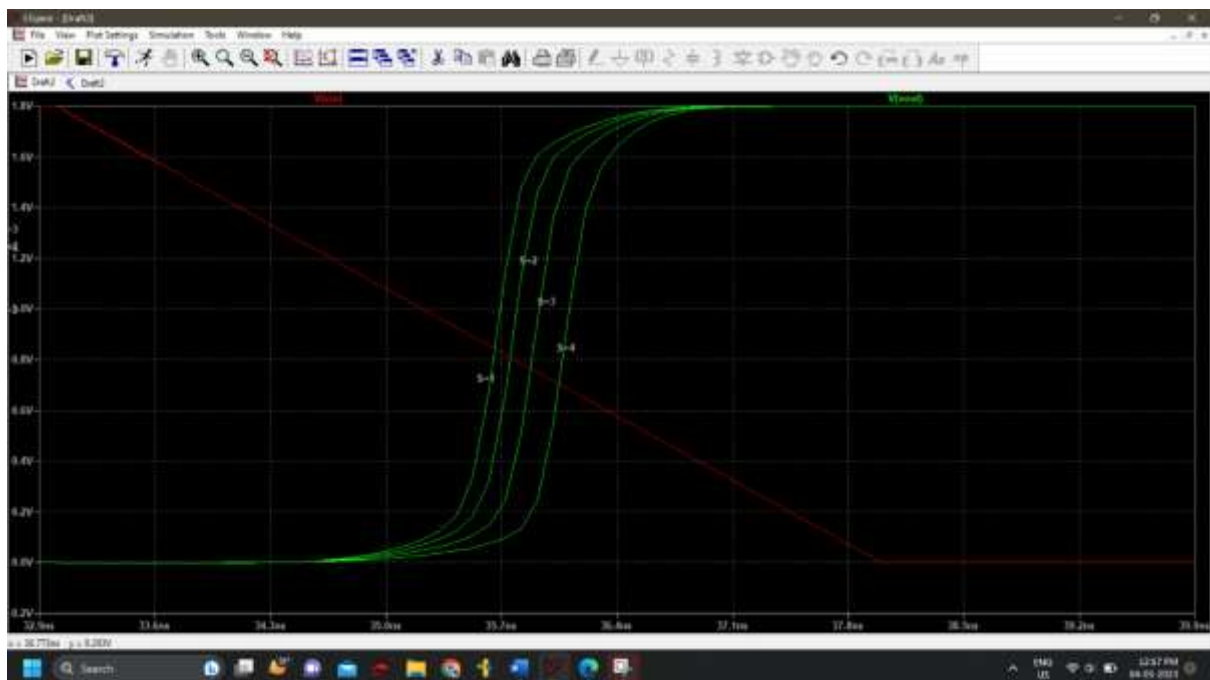
Without capacitor at output node

Measurement: t_{hl}

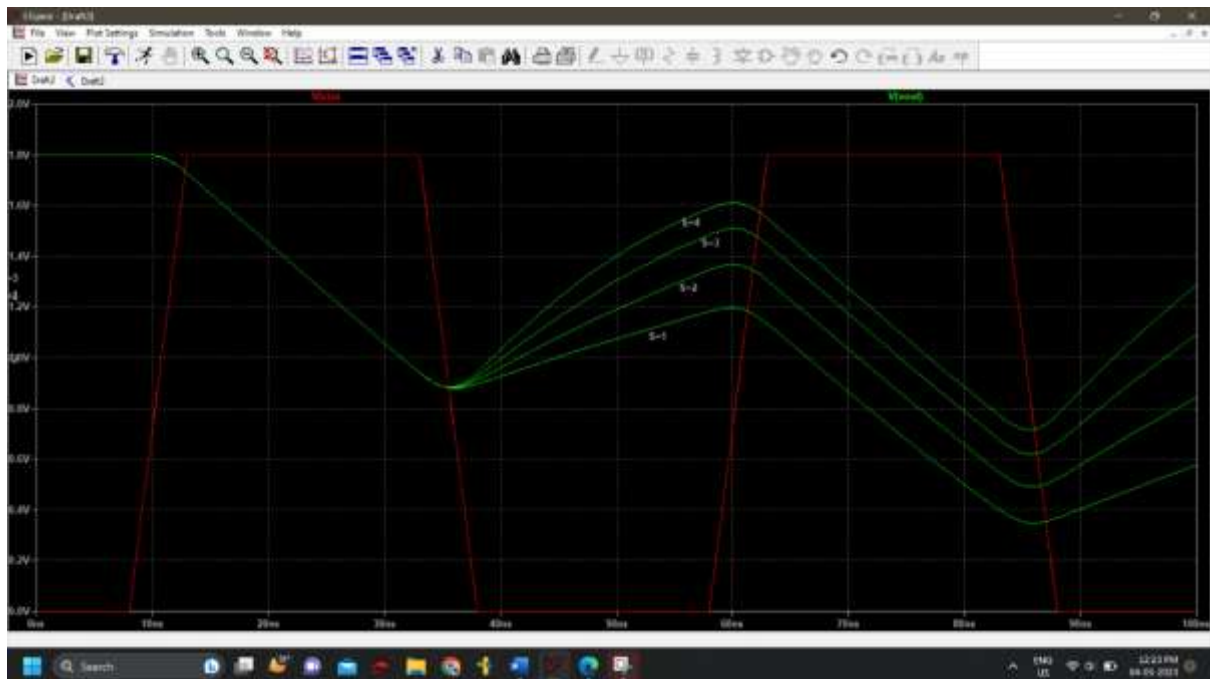
step	t_{hl}	FROM	TO
1	5.31521e-10	9.64719e-09	1.01787e-08
2	5.52082e-10	9.82774e-09	1.03798e-08
3	5.64594e-10	9.96823e-09	1.05328e-08
4	5.57457e-10	1.00857e-08	1.06432e-08

Measurement: t_{lh}

step	t_{lh}	FROM	TO
1	5.16693e-10	3.58572e-08	3.63739e-08
2	5.39519e-10	3.56547e-08	3.61942e-08
3	5.3232e-10	3.55239e-08	3.60562e-08
4	5.25373e-10	3.54154e-08	3.59408e-08



With capacitor at output node

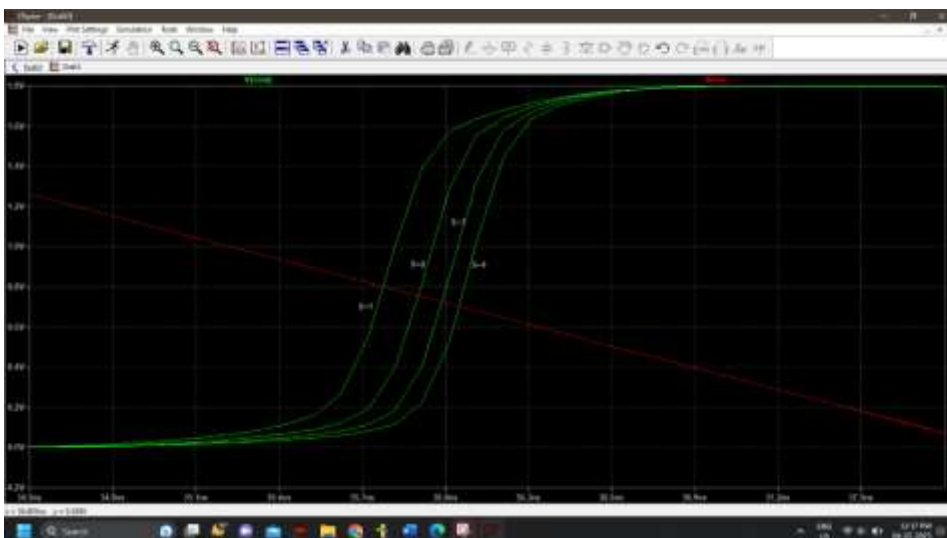


Measurement "t_hl" FAIL'ed

Measurement "t_lh" FAIL'ed

When NMOS is sized K_n times the size of the corresponding NMOS of the minimum-sized inverter for $K_n = 1, 2, 4$, keeping the size of the PMOS the same as that of the corresponding PMOS of the minimum-sized inverter.

Without capacitor



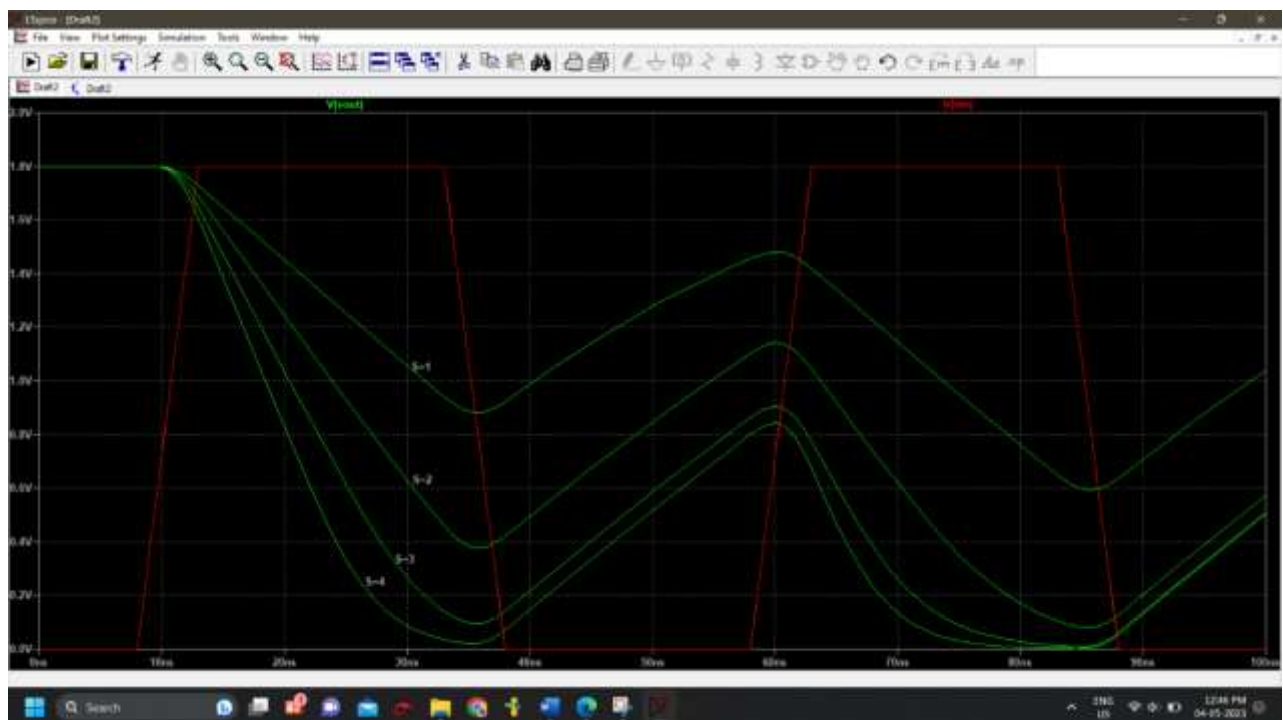
Measurement: t_{hl}

step	t _{hl}	FROM	TO
1	5.49713e-10	9.9379e-09	1.04876e-08
2	5.14946e-10	9.84303e-09	1.0358e-08
3	4.81481e-10	9.77937e-09	1.02609e-08
4	4.52877e-10	9.73166e-09	1.01845e-08

Measurement: t_{lh}

step	t _{lh}	FROM	TO
1	5.42273e-10	3.55436e-08	3.60858e-08
2	4.79771e-10	3.57049e-08	3.61847e-08
3	4.42384e-10	3.58119e-08	3.62543e-08
4	4.24381e-10	3.58762e-08	3.63006e-08

With capacitor

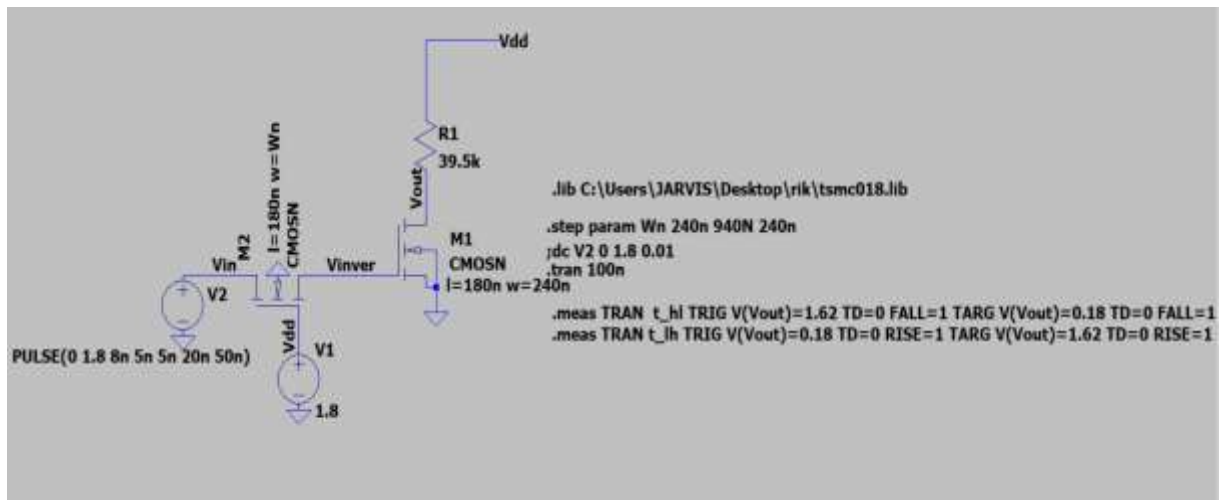


Measurement: t_{hl}

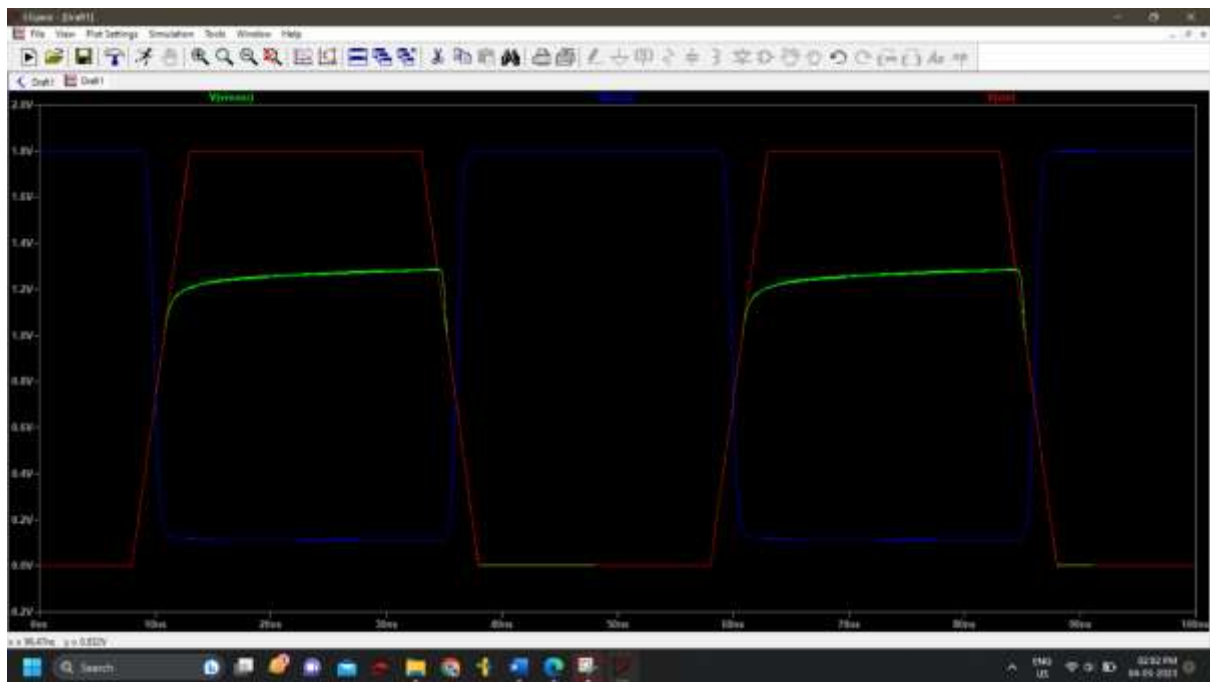
step	t _{hl}	FROM	TO
1	0	1.57354e-08	0
2	6.55689e-08	1.40724e-08	7.96413e-08
3	1.86163e-08	1.33046e-08	3.19209e-08
4	1.45775e-08	1.2857e-08	2.74345e-08

Measurement "t_{lh}" FAIL'ed

e)



External resistance used to make the rise and fall time equal is 39.5 k-ohms

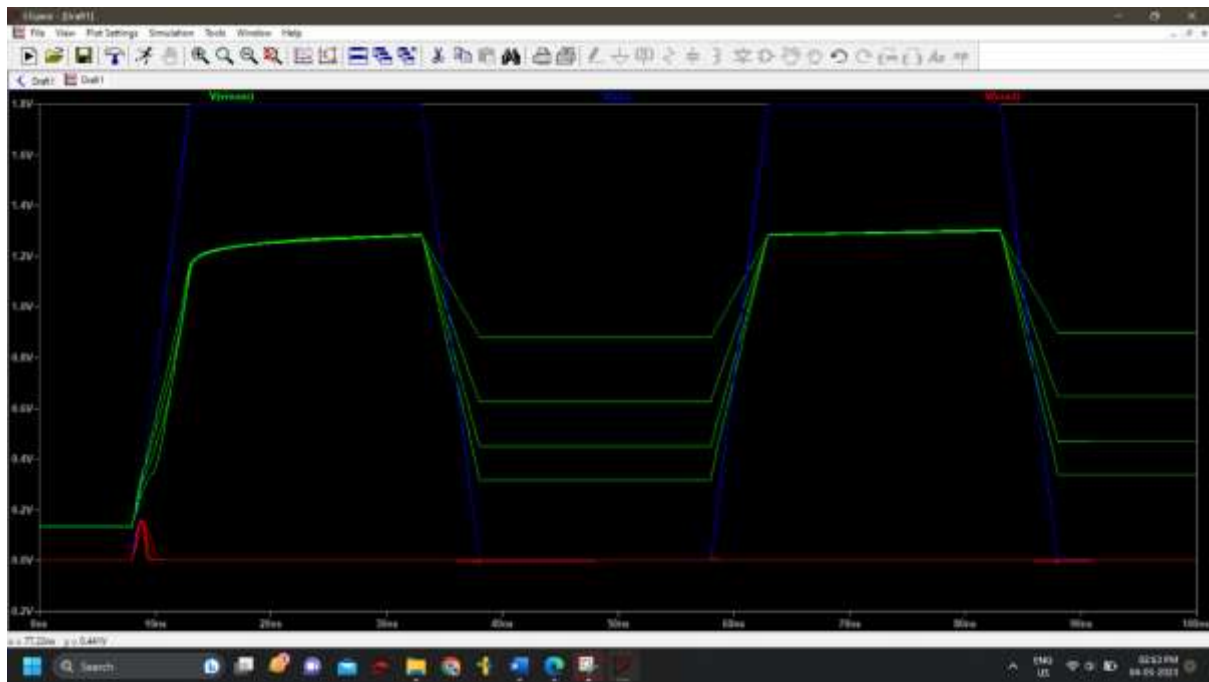


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Measurement: t_hl
step    t_hl FROM TO
1       1.29995e-09 9.38816e-09 1.06881e-08
2       1.29898e-09 9.38727e-09 1.06862e-08
3       1.29847e-09 9.38686e-09 1.06853e-08
4       1.29828e-09 9.38664e-09 1.06849e-08

Measurement: t_lh
step    t_lh FROM TO
1       1.29691e-09 3.53464e-08 3.66433e-08
2       1.29793e-09 3.53445e-08 3.66424e-08
3       1.29844e-09 3.53436e-08 3.6642e-08
4       1.29874e-09 3.5343e-08 3.66418e-08

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Measurement "t_hl" FAIL'ed
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Measurement "t_lh" FAIL'ed
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We are not getting any rise time or fall time because the pass transistor turns off at $V_{DD} - V_T$ which is $1.8 - 0.366$ so, the output will never reach 90% of the input.